## Direct synthesis and characterization of graphene layers on silicon dioxide substrates

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Direct synthesis of graphene on semiconductors and dielectric substrates is of high interest as this process bypasses typical transfer procedures, which usually uses polymers as sacrifice layers along with toxic chemicals and it leaves out residues that often damages the graphene flakes as well. The interest of direct graphene synthesis comes as high yield, electronic arade araphene is only possible bv eliminating the transfer process and tuning the growth process to maximize graphene quality. We worked on the direct synthesis of graphene layers on silica glass and silicon dioxide wafers substrates by vapor deposition chemical at semiatmospheric pressure environment inside the tube reactor, using controlled mixtures of hydrogen, argon and methane gases. The effects of the methane flux and the total pressure on the homogeneity of the graphene layers were investigated. The samples were characterized using Raman scattering spectroscopy and Raman mapping, Atomic force microscopy, X-ray photoelectron spectroscopy and optical transmittance measurements and sheet resistivity measurements. Large area, homogeneous bilayer graphene was obtained for an appropriate gas mixture and Raman spectroscopy results indicate that misoriented graphene bilayers were obtained.

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## Figures







